# High Performance Computing Infrastructure (HPCI) and Software Development

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# **HPCI** (High Performance Computing Infrastructure)

High-Performance Computing Infrastructure (HPCI) is a shared computational environment in Japan. The mission of HPCI is to realize the scientific and technological computing environment where a wide range of HPC users in Japan can access national HPC resources efficiently.



Figure 1: Organizations engaging in the HPCI system operation (Fiscal Year 2019)

## FLAGSHIP 2020 Project (FY2015-2019)



http://www.aics.riken.jp/en/postk/project

### 9 priority issues in FLAGSHIP 2020 Project



http://www.aics.riken.jp/fs2020p/en/

## CDMSI (FY2015-2019)





### Creation of new functional Devices and high-performance Materials to Support next-generation Industries

The Institute for Solid State Physics, the University of Tokyo

and 9 other institutes:

Institute for Materials Research (Tohoku Univ.), Institute for Molecular Science, University of Tsukuba, Osaka University, Nagoya University, Nagoya Institute of Technology, Yokohama National University, Tokyo University of Science, National Institute of Advanced Industrial Science and Technology



http://www.aics.riken.jp/fs2020p/en/

## Sub-issues in CDMSI (FY2015-2019)

Vethod	s Device	
<b>ods</b> for nulation	Sub-issue A: New-functionality and high- performance <b>semiconductor</b> <b>devices</b>	
<b>meth</b> nce sim	Sub-issue B: Unified photonic-electronic devices	
<b>1ental</b> Is scier	Sub-issue C: <b>Superconductors</b> and new functional devices and materials	
<b>dan</b> erial	Materials	
le G: <b>Fun</b> mate	Sub-issue D: High performance permanent magnets and magnetic materials Sub-issue F: Advanced structural materials	
Sub-issu	Sub-issue F: Next-generation functional chemical substance	/?!!??
	Sub-issue G: Fundamental methods for materials science simulation	Vethods Device   Joint Structure Sub-issue A: New-functionality and high-performance semiconductor devices   Sub-issue B: Unified photonic-electronic devices   Sub-issue C: Superconductors and new functional devices and materials   Sub-issue C: Superconductors and new functional devices and materials   Sub-issue D: High performance permanent magnets and magnetic materials   Sub-issue E: Advanced structural materials   Sub-issue F: Next-generation functional chemical substance



# A portal site for materials science simulation





4300 users, >16000 pageview / month (FY2019) 2116 users, 11267 pageview / month (FY2018)

# **OpenMX** http://www.openmx-square.org

- A software package for electronic-structure calculation based on Density Functional Theory (DFT)
- Norm-conserving pseudopotentials
- Variationally optimized numerical atomic basis functions
- Besides basic functions, the package is equipped with
  - O(N) method
  - Calculation of Magnetic anisotropy energy (MAE),
  - Exchange coupling parameters,
  - Z2 & Chern topological invariant,
  - Core level calculations for XPS
  - Interface with BoltzTrap

and many other functions





Main Contributor: Taisuke Ozaki (ISSP, U. Tokyo)

## Appendix

# New features in OpenMX Ver. 3.9

### Taisuke Ozaki (ISSP, Univ. of Tokyo) Dec. 3, 2019

# **OpenMX Open** source package for Material eXplorer



- Software package for density functional calculations of molecules and bulks
- Norm-conserving pseudopotentials (PPs)
- Variationally optimized numerical atomic basis functions

#### Basic functionalities

- SCF calc. by LDA, GGA, DFT+U
- Total energy and forces on atoms
- Band dispersion and density of states
- Geometry optimization by BFGS, RF, EF
- Charge analysis by Mullken, Voronoi, ESP
- Molecular dynamics with NEV and NVT ensembles
- Charge doping
- Fermi surface
- Analysis of charge, spin, potentials by cube files
- Database of optimized PPs and basis funcitons

#### Extensions

- O(N) and low-order scaling diagonalization
- Non-collinear DFT for non-collinear magnetism
- Spin-orbit coupling included self-consistently
- Electronic transport by non-equilibrium Green function
- Electronic polarization by the Berry phase formalism
- Maximally localized Wannier functions
- Effective screening medium method for biased system
- Reaction path search by the NEB method
- Band unfolding method
- STM image by the Tersoff-Hamann method
- etc.

# New features in OpenMX Ver. 3.9



- Database 2019 of PAO and VPS (Ozaki)
- Database 2019 of PAO and VPS for core level excitation (Ozaki)
- Core level calculations for XPS (Ozaki)
- O(N) DC-LNO method (Ozaki)
- Calculations of gaseous charged systems (Ozaki)
- Complex dielectric function & optical conductivity tensors (YTL)
- Spin texture for Rashba effect (Kotaka, Yamaguchi, Ishii)
- Generalized Bloch theorem for spin spiral (Prayitno, Ishii)
- Z2 & Chern topological invariant (Sawahata, Ishii)
- Improvement of polB (Yamaguchi)
- Second variational scheme of SOI (Po-Hao Chang)
- Efficient implementation of j<sub>ij</sub> (Terasawa)
- Optimization of enthalpy (Ozaki)
- New DFT+U functionals (Ryee&Han)
- Mixing methods of DIISV (Ozaki)
- ELPA1/ELPA2 (Duy and Ozaki)
- OpenMX engine by MPI\_spawn (Ozaki)
- Jx (Yoon, Kim, Sim, Han)
- Interface with FermiSurfer (Kawamura)
- Interface with BoltzTrap (Miyata)
- Interface with ASE (Yu)

### Second variational scheme for evaluation of magnetic anisotropy energy (MAE) supported by P.-H. Chang and Ozaki



A second variational method is supported to calculate band structures modified with spin-orbit coupling (SOI) and magnetic anisotropy energy (MAE).



# Second variational scheme

- First, the SCF calculation is performed by the collinear DFT
- Second, with the SCF charge the one-shot diagonalization is performed with SOI.
- The total energy is evaluated by the Harris functional.

# Efficient calculations of exchange coupling parameters supported by Terasawa, Ozaki, and Gohda



A post-processing code 'jx' to calculate exchange coupling parameters  $J_{ij}$  has been largely improved so that the individual  $J_{ij}$  in bulks can be calculated efficiently using a contour integration method.







(b) hcp Co, k-grid =  $32 \times 32 \times 20$ 

### **Currie temperature**

	$T_{\rm C}$ [K]		
System	calculated	experimental	
bcc Fe	1321	1040	
hcp Co	1640	1131	
fcc Ni	445	627	

A Terasawa, M Matsumoto, T Ozaki, and Y Gohda, J. Phys. Soc. Jpn. **88**, 114706 (2019).

# Chern number, Berry curvature, and Z<sub>2</sub> invariant supported by Sawahata and Ishii



In OpenMX Ver. 3.9, a post-processing code 'calB' is supported to calculate the Chern number and Berry curvature of bands using overlap matrix elements between Kohn-Sham orbitals at neighboring k-points by the Fukui-Hatsugai-Suzuki method. The Chern number is a topological invariant being an integer number, which characterizes the topology of bands for any materials. We also release another post-processing code 'Z2FH' to calculate the  $Z_2$  topological invariant using the Berry phase by the Fukui-Hatsugai method.



0.3

0.4

-0.2

Berry curvature for bands of graphene



H. Sawahata, N. Yamaguchi, H. Kotaka, and F. Ishii, Jpn. J. Appl. Phys. 57, 030309 (2018).

### Absolute binding energies of core levels XPS core level energies supported by Ozaki



A general method has been supported to calculate absolute binding energies of core levels in metals and insulators, based on a penalty functional and an exact Coulomb cutoff method in the framework of density functional theory. With the method one can treat multiple splittings due to chemical shift, spin-orbit coupling, and exchange interaction on equal footing.

$$E_{\rm b} = E_{\rm f}^{(0)}(N-1) - E_{\rm i}^{(0)}(N) + \mu_0$$

**Penalty functional** 

$$E_{\rm f} = E_{\rm DFT} + E_{\rm p}$$

#### Exact Coulomb cutoff method



Material	State	Calc. $(eV)$	Expt. (eV)
Gapped system			
c-BN	N-1 <i>s</i>	398.87	$398.1^{*}$
bulk $\rm NH_3$	N-1 <i>s</i>	398.92	$399.0^{+}$
Diamond	C-1s	286.50	$285.6^{\dagger}$
Si	$Si-2p_{1/2}$	100.13	99.8*
Si	$Si-2p_{3/2}$	99.40	$99.2^{*}$
Semimetal or Me	tal		
Graphene	C-1 <i>s</i>	284.23	$284.4^{\dagger}$
TiN	N-1 <i>s</i>	396.43	397.1 <sup>§</sup>
TiC	C-1 <i>s</i>	281.43	$281.5^{*}$

Mean absolute error: 0.4 eV, Mean relative error: 0.16 %

T. Ozaki and C.-C. Lee, Phys. Rev. Lett. 118, 026401 (2017) 5

### Interface with BoltzTrap supported by Miyata



OpenMX is interfaced with BoltzTraP which calculates electron transport coefficients based on the Boltzmann theory from the wave number dependence of the energy eigenvalues in the Kohn-Sham equation. The interface with BoltzTraP enables us to calculate physical properties such as the Seebeck coefficient, electrical conductivity, electronic thermal conductivity, and the Hall coefficient. The functionality is compatible with not only the collinear calculations, but also the non-collinear calculations.



Figure 78: (a) Seebeck coefficient S, and (b) the electric conductivity  $\sigma \tau_{\rm el}^{-1}$  of non-doped Si in the diamond structure as a function of the chemical potential at 300 K obtained by OpenMX and BoltzTraP. The Fourier interpolation factor was set to 25. The input file 'Si\_BoltzTraP.dat' used for the calculation is available in the directory 'work'.